

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

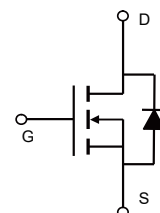
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 100V, I_D = 65A$
 $R_{DS(ON)} = 9m\Omega$, typical@ $V_{GS} = 10V$
 $R_{DS(ON)} = 11m\Omega$, typical@ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating



TO-220



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST10N090	VST10N090-TC	TO-220	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	65	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	45.5	A
Pulsed Drain Current	I_{DM}	260	A
Maximum Power Dissipation	P_D	100	W
Derating factor		0.6	W/ $^\circ C$
Single pulse avalanche energy (Note 4)	E_{AS}	288	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	$^\circ C/W$
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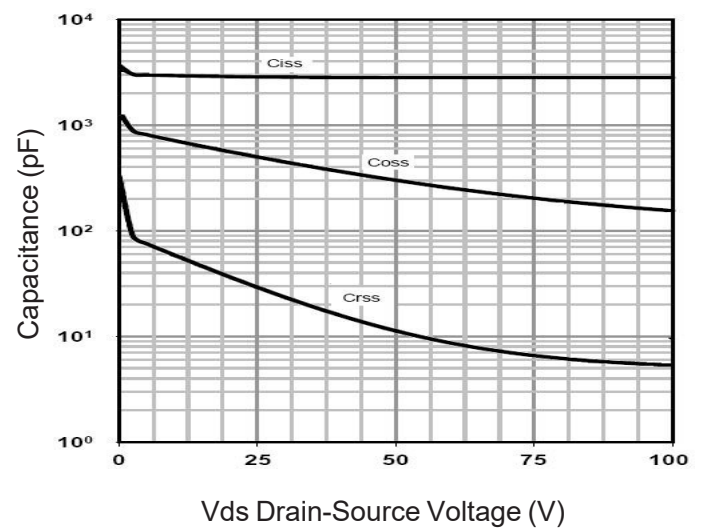
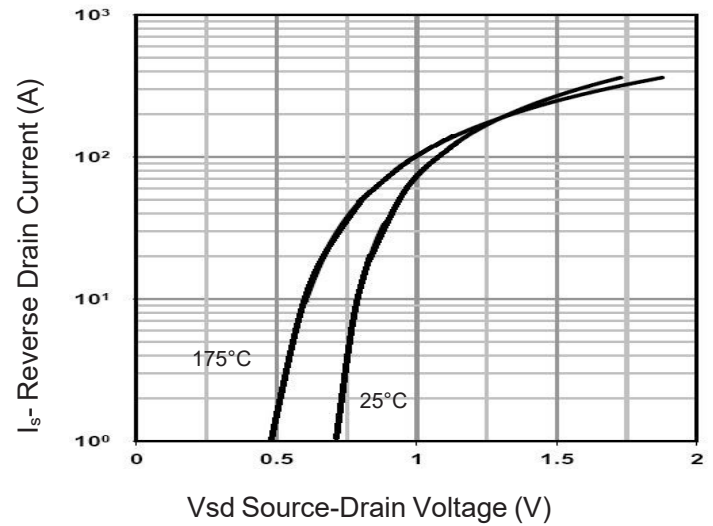
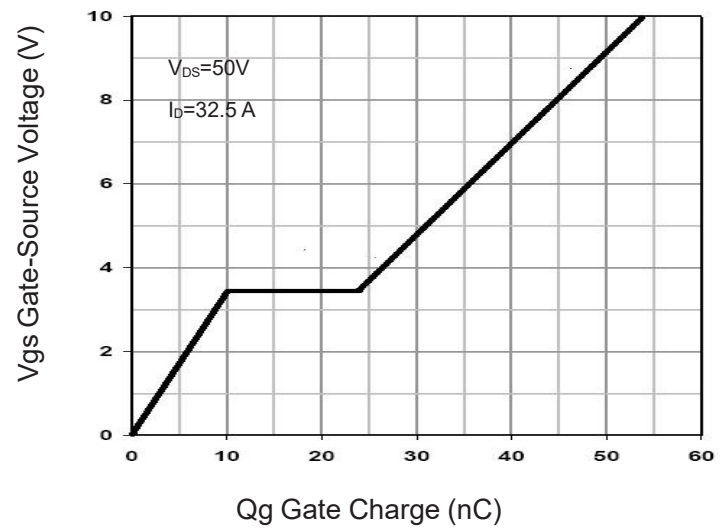
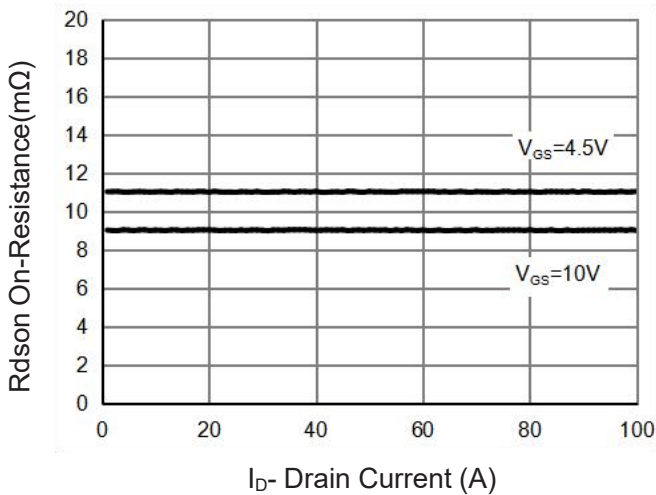
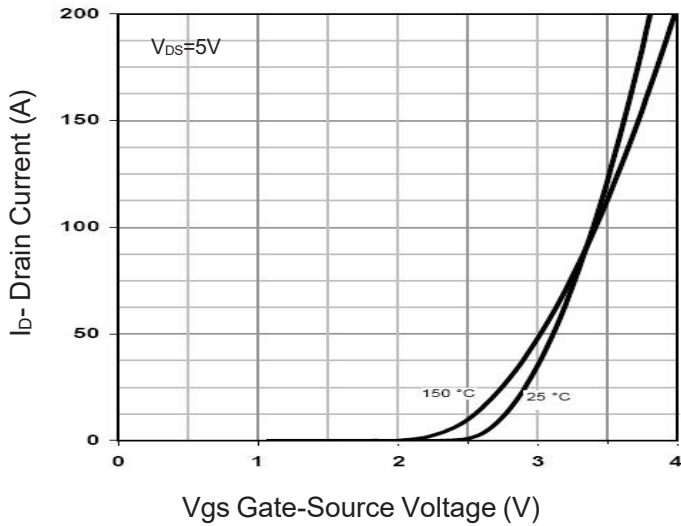
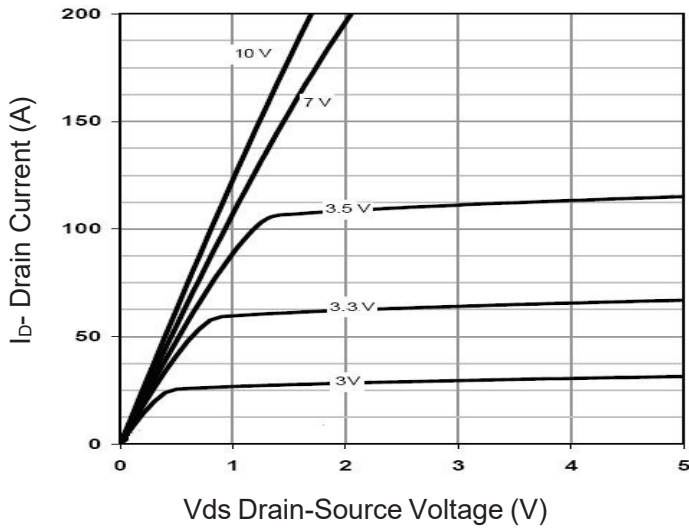
Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	1.7	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =32.5A	-	9	9.5	mΩ
		V _{GS} =4.5V, I _D =32.5A	-	11	12.5	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =32.5A		50	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	2609	-	pF
Output Capacitance	C _{oss}		-	247.5	-	pF
Reverse Transfer Capacitance	C _{rss}		-	17	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =32.5A V _{GS} =10V, R _G =1.6Ω	-	13	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =32.5A, V _{GS} =10V	-	45	-	nC
Gate-Source Charge	Q _{gs}		-	9.4	-	nC
Gate-Drain Charge	Q _{gd}		-	10.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V, I _S =32.5A	-	-	1.2	V
Diode Forward Current	I _S		-	-	65	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 32.5A di/dt = 100A/μs (Note3)	-	55	-	nS
Reverse Recovery Charge	Q _{rr}		-	98	-	nC

Notes:

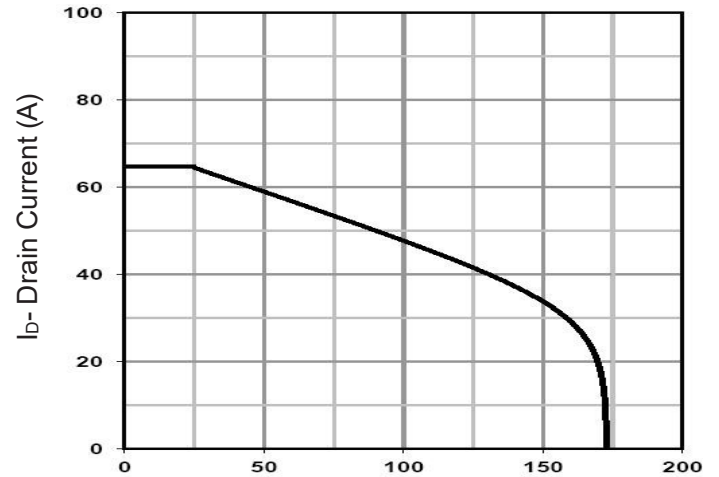
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production
4. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

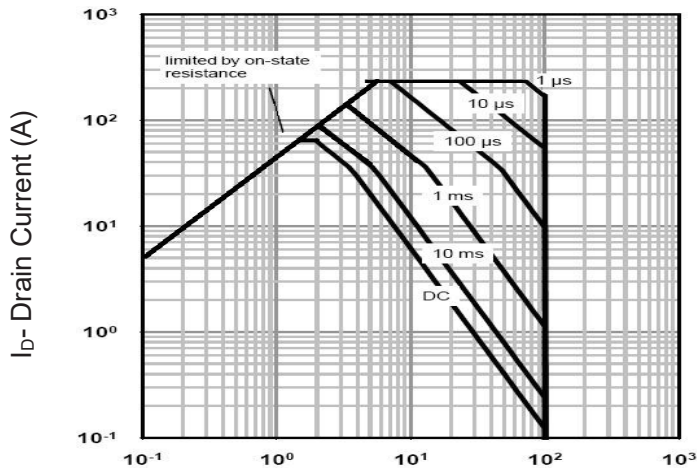




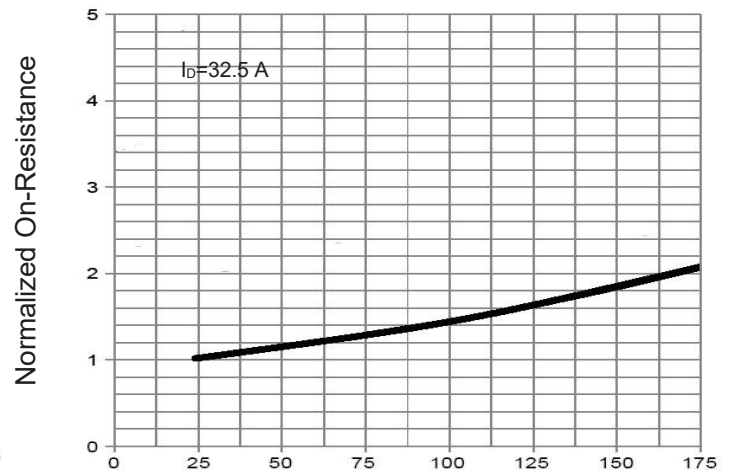
T_J -Junction Temperature(°C)
Figure 7 Power De-rating



T_J -Junction Temperature (°C)
Figure 9 Current De-rating



V_{ds} Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J -Junction Temperature(°C)
Figure 10 Rdson-Junction Temperature

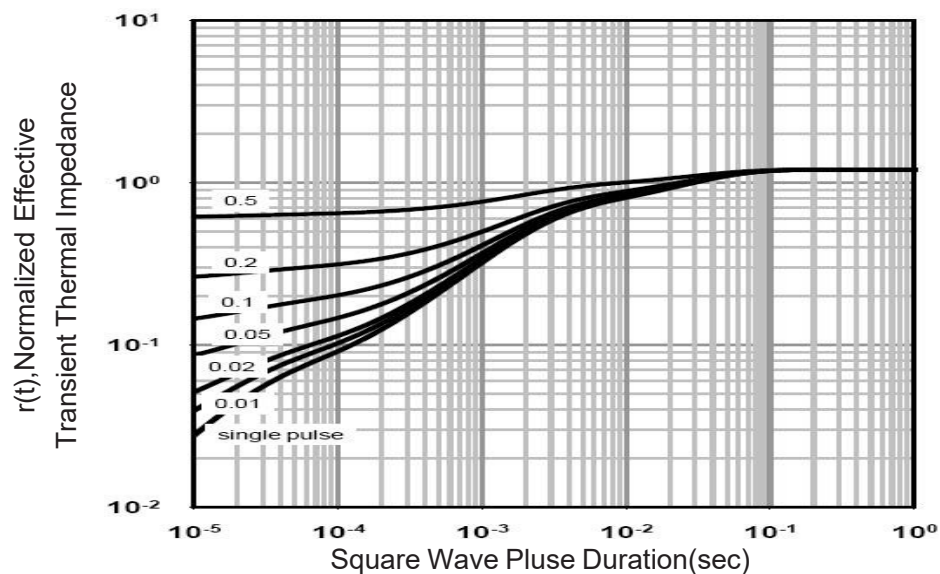


Figure 11 Normalized Maximum Transient Thermal Impedance